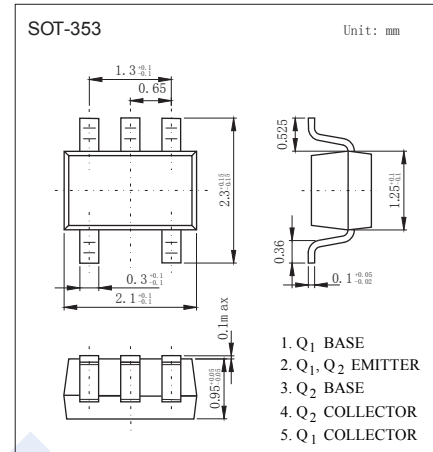
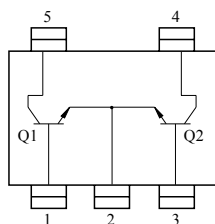


NPN Transistors

KTC601U

■ Features

- Excellent temperature response between these 2 transistor.
- High pairing property in hFE.
- The following characteristics are common for Q1, Q2.



■ Absolute Maximum Ratings Ta = 25°C

Parameter	Symbol	Rating	Unit
Collector - Base Voltage	V _{CB0}	60	V
Collector - Emitter Voltage	V _{CEO}	50	
Emitter - Base Voltage	V _{EB0}	5	
Collector Current - Continuous	I _C	150	mA
Base Current	I _B	30	
Collector Power Dissipation	P _C	200	mW
Junction Temperature	T _J	150	°C
Storage Temperature Range	T _{stg}	-55 to 150	

■ Electrical Characteristics Ta = 25°C

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector- base breakdown voltage	V _{CB0}	I _C = 100 μA, I _E = 0	60			V
Collector- emitter breakdown voltage	V _{CEO}	I _C = 1 mA, I _B = 0	50			
Emitter - base breakdown voltage	V _{EB0}	I _E = 100 μA, I _C = 0	5			
Collector-base cut-off current	I _{CB0}	V _{CB} = 60 V, I _E = 0			0.1	μA
Emitter cut-off current	I _{EB0}	V _{EB} = 5V, I _C =0			0.1	
Collector-emitter saturation voltage	V _{CE(sat)}	I _C =100 mA, I _B =10mA			0.25	V
Base - emitter saturation voltage	V _{BE(sat)}	I _C =100 mA, I _B =10mA			1.2	
DC current gain	h _{FE}	V _{CE} = 6V, I _C = 2 mA	120		400	
Noise Figure	NF	V _{CE} =6V, I _C =0.1mA, f=1KHz, R _g =10KΩ			10	dB
Collector output capacitance	C _{ob}	V _{CB} = 10V, I _E = 0, f=1MHz			3.5	pF
Transition frequency	f _T	V _{CE} = 10V, I _C = 1mA	80			MHz

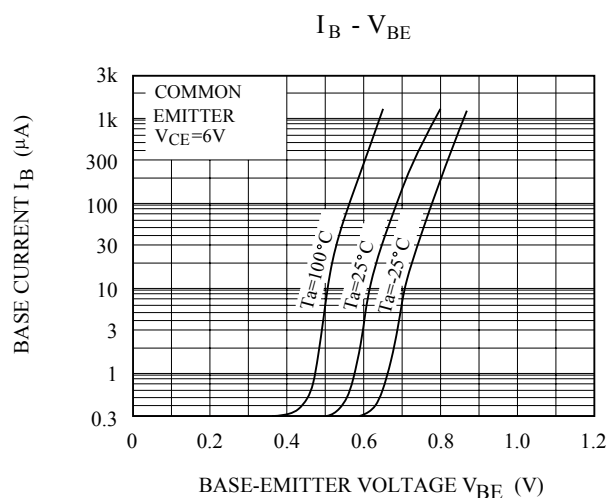
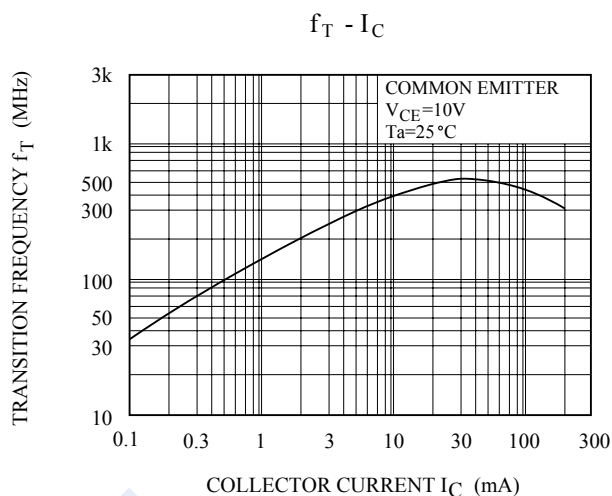
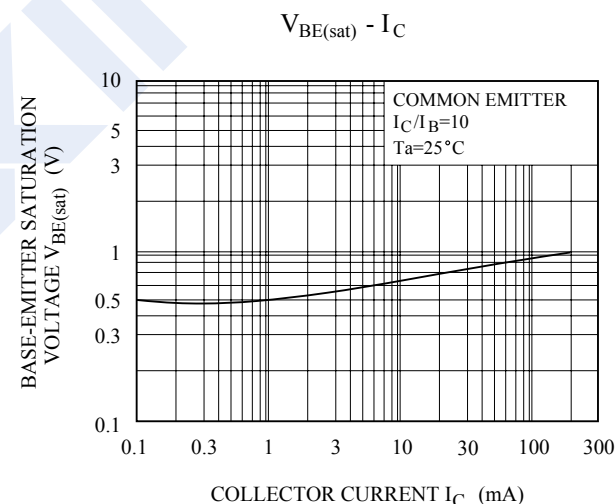
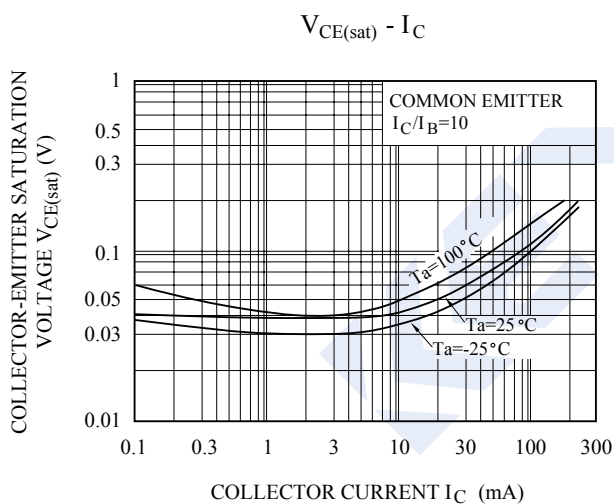
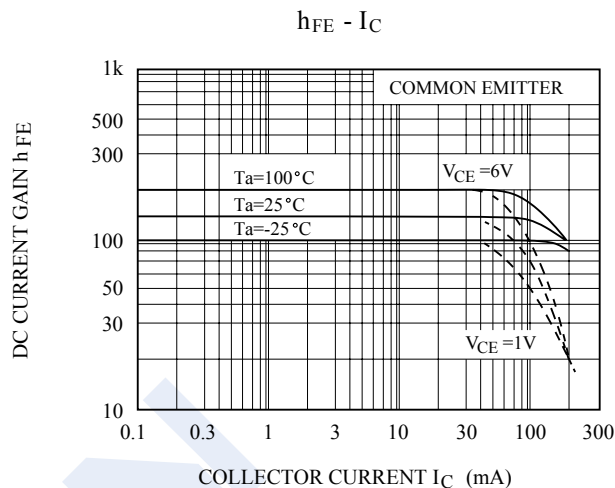
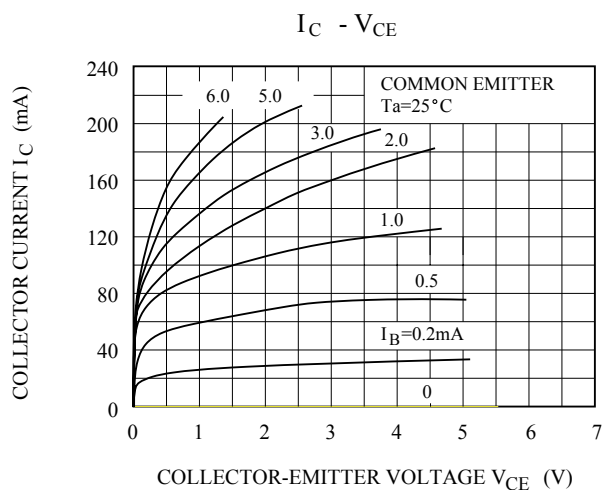
■ Classification of hfe

Type	KTC601U-Y	KTC601U-G
Range	120-240	200-400
Marking	LY	LG

NPN Transistors

KTC601U

■ Typical Characteristics



NPN Transistors

KTC601U

■ Typical Characteristics

